WHAT IS CLAIMED IS:

1. A liquid crystal display device comprising:

a gate electrode, a gate pad and gate links on a substrate, the gate links having gate dummy patterns;

a gate insulating film on the gate electrode and the gate link;

a semiconductor layer on the gate insulating film;

a source electrode, a drain electrode, a data pad and data links on the semiconductor layer;

a protective film on the source and drain electrodes and the data link; and

a pixel electrode on the protective film.

2. The device of claim 1, wherein the gate links and the gate dummy patterns include a same height.

3. The device of claim 1, wherein each of the gate links includes the gate electrode, the gate insulation film, the semiconductor layer, and the protective film.

4. The device of claim 1, further comprising a sealant on the gate links and the data links.

5. The device of claim 1, further comprising data dummy patterns between the data links.

6. The device of claim 5, wherein the data links and the data dummy patterns include a same height.

7. The device of claim 5, wherein each of the data links includes the source and drain electrodes, the gate insulation film, the semiconductor layer, and the protective film.

8. The device of claim 1, wherein the semiconductor layer includes a doped semiconductor layer.

9. A method of fabricating a liquid crystal display device, comprising:

forming a gate electrode, a gate pad and gate links on a substrate, the gate links having gate dummy patterns;

forming a gate insulating film on the gate electrode and the gate link;

forming a semiconductor layer on the gate insulating film;

forming a source electrode, a drain electrode, a data pad and data links on the semiconductor layer;

forming a protective film on the source and drain electrodes and the data link; and

forming a pixel electrode on the protective film.

10. The method of claim 9, wherein the gate links and the gate dummy patterns include a same height.

11. The method of claim 9, wherein each of the gate links includes the gate electrode, the gate insulation film, the semiconductor layer, and the protective film.

12. The method of claim 9, further comprising the step of forming a sealant on the gate links and the data links.

13. The method of claim 9, further comprising the step of forming data dummy patterns between the data links.

14. The method of claim 13, wherein the data links and the data dummy patterns include a same height.

15. The method of claim 13, wherein each of the data links includes the source and drain electrodes, the gate insulation film, the semiconductor layer, and the protective film.

16. The method of claim 9, wherein the semiconductor layer includes a doped semiconductor layer.

17. A method of fabricating a liquid crystal display device, comprising:

forming a gate electrode, a gate pad and gate links on a substrate, the gate links having gate dummy patterns;

forming a gate insulating film a semiconductor layer on the gate electrode and the gate link;

forming a source electrode, a drain electrode, a data pad and data links on the semiconductor layer;

forming a protective film on the source and drain electrodes and the data link; and

patterning the gate insulating film, the semiconductor layer, and the protective film; and

forming a pixel electrode on the protective film.

18. The method of claim 17, wherein the gate links and the gate dummy patterns include a same height.

19. The method of claim 17, wherein each of the gate links includes the gate electrode, the gate insulation film, the semiconductor layer, and the protective film.

20. The method of claim 17, further comprising the step of forming a sealant on the gate links and the data links.

21. The method of claim 17, further comprising the step of forming data dummy patterns between the data links.

22. The method of claim 21, wherein the data links and the data dummy patterns include a same height.

23. The method of claim 21, wherein each of the data links includes the source and drain electrodes, the gate insulation film, the semiconductor layer, and the protective film.

24. The method of claim 17, wherein the semiconductor layer includes a doped semiconductor layer.